

AMENDMENTS TO THE SPECIFICATION (other than claims)

Please replace the paragraph beginning at page 4, line 8, which starts with "Fig. 1 is a schematic sectional view," with the following amended paragraph:

Fig. 1 is a schematic sectional view illustrating one specific example of a ceramic susceptor according to the present invention; [[and]]

Please replace the paragraph beginning at page 4, line 10, which starts with "Fig. 2 is a schematic sectional view," with the following amended paragraph:

Fig. 2 is a schematic sectional view illustrating a separate specific example of a ceramic susceptor according to the present invention[[.]]; and

Please add the following new paragraph after the paragraph beginning at page 4, line 10, which starts with "Fig. 2 is a schematic sectional view":

Fig. 3 is a lateral and a plan view, not to scale, of a wafer on a susceptor according to the present invention, illustrating average outer diameter of the susceptor wafer-support side, and the maximum and minimum susceptor outer diameters along the thickness in an arbitrary plane.

Please replace the paragraph beginning at page 5, line 19, which starts with "More specifically, letting D_{ave} ," with the following amended paragraph:

More specifically, as illustrated representatively in Fig. 3, letting D_{ave} be the average outer diameter of the ceramic susceptor wafer-support side, and D_{max} and D_{min} be the maximum and minimum susceptor outer diameters along the thickness in

an arbitrary plane, then the outer-diameter fluctuation parameter D_p is defined as $D_p = (D_{max} - D_{min})/D_{ave}$. By thus controlling outer-diameter fluctuation parameter D_p to 0.8% or less, the temperature uniformity of the wafer surface can be brought within $\pm 0.5\%$ in ceramic susceptors whose thermal conductivity is 100 W/mK or more, and within $\pm 1.0\%$ in ceramic susceptors whose thermal conductivity is 10 to 100 W/mK.

Please replace the paragraph beginning at page 8, line 13, which starts with "It will be understood that here," with the following amended paragraph:

It will be understood that here the outer-diameter fluctuation parameter D_p is defined as $D_p = (D_{max} - D_{min})/D_{ave}$, wherein, as represented in Fig. 3, respectively D_{ave} represents the average outer diameter of the ceramic susceptor wafer-support side, D_{max} , the maximum outer diameter along the thickness in an arbitrary plane; and D_{min} , the minimum outer diameter along the thickness in the arbitrary plane (likewise in all of the embodiments hereinafter).